

Fig. 35B-4-001. $\text{KTi}_{1-x}\text{Nb}_x\text{OP}_{1-x}\text{Si}_x\text{O}_4$. a , b , c , V vs. x [93Ran]. V : unit cell volume.

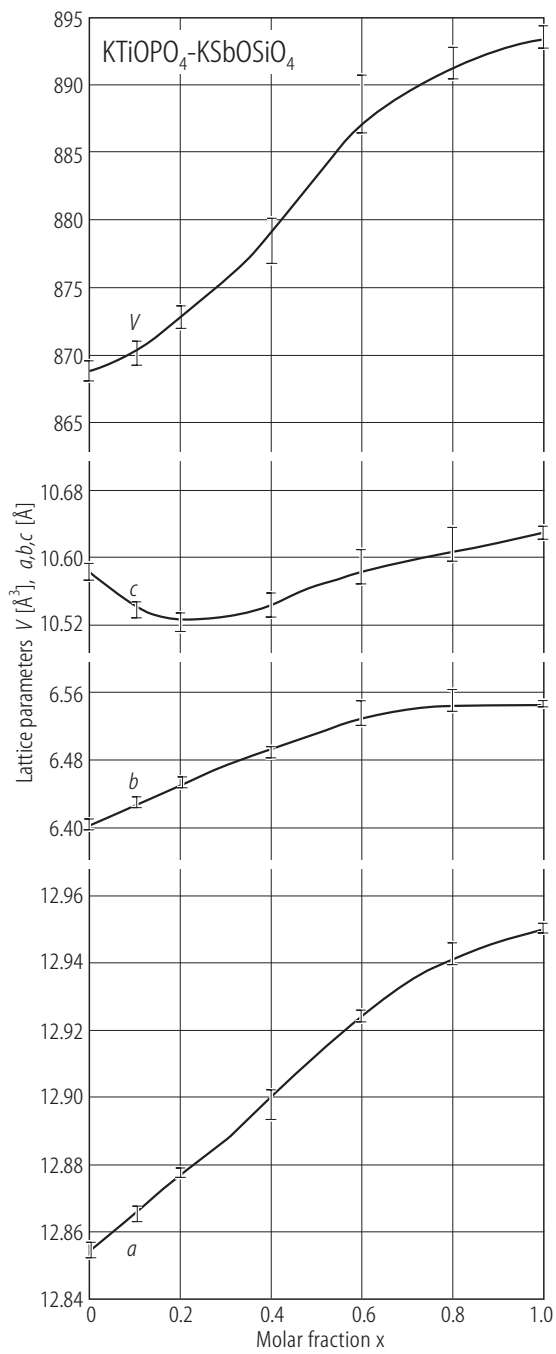


Fig. 35B-4-002. $\text{KTi}_{1-x}\text{Sb}_x\text{OP}_{1-x}\text{Si}_x\text{O}_4$ (ceramics). a , b , c , V vs. x [91Rav]. V : unit cell volume.

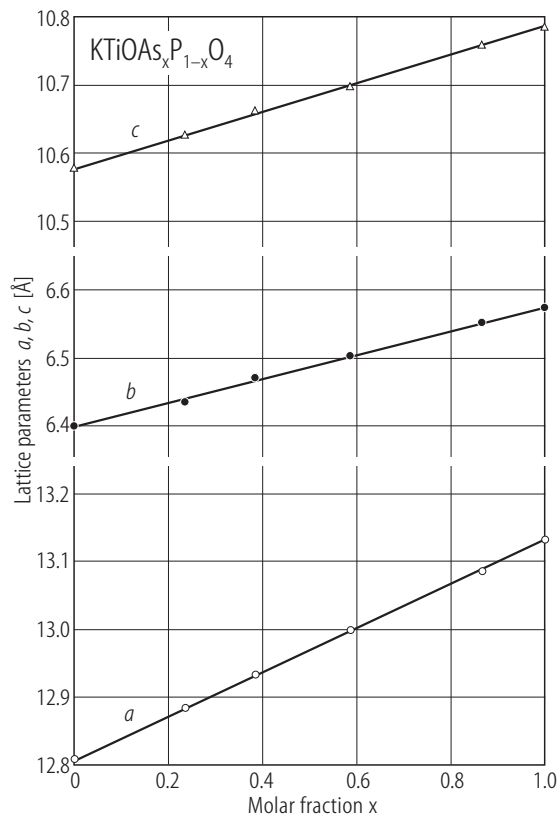


Fig. 35B-4-003. $\text{KTiOP}_{1-x}\text{As}_x\text{O}_4$. a , b , c vs. x [91Che]. Thin films grown by liquid phase epitaxy.

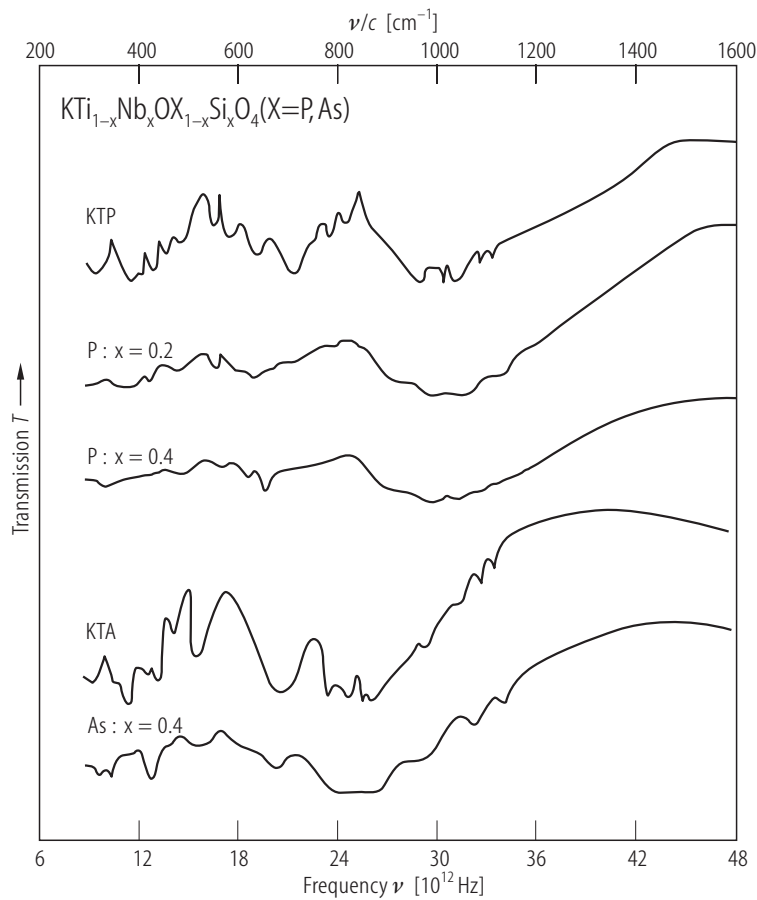


Fig. 35B-4-004. $\text{KTi}_{1-x}\text{Nb}_x\text{OX}_{1-x}\text{Si}_x\text{O}_4$ ($X = \text{P}, \text{As}$). T vs. ν [93Ran]. T : infrared transmittance. KTP = KTiOPO_4 , KTA = KTiOAsO_4 .

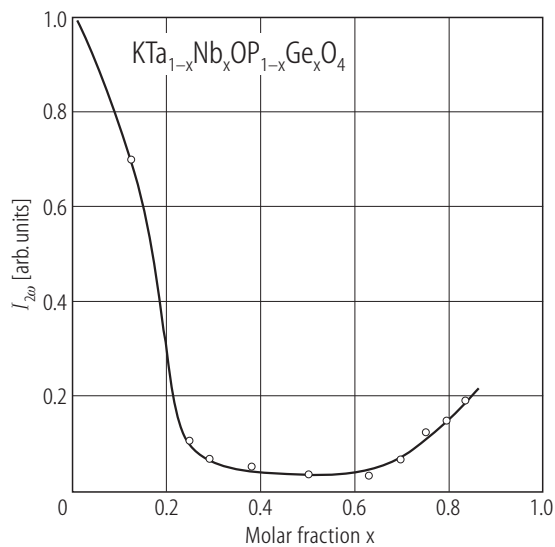


Fig. 35B-4-005. $\text{KTa}_{1-x}\text{Nb}_x\text{OP}_{1-x}\text{Ge}_x\text{O}_4$. $I_{2\omega}$ vs. x [94But]. $\lambda = 1064 \text{ nm}$. $I_{2\omega}$: SHG power (relative intensity).